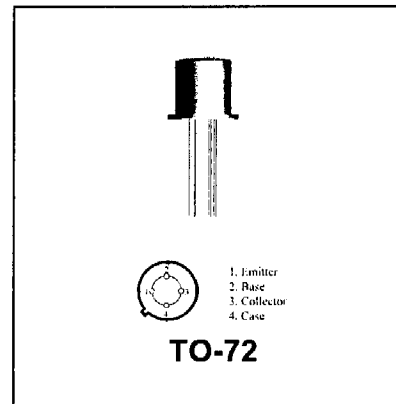


**2N5031**

**RF & MICROWAVE DISCRETE  
LOW POWER TRANSISTORS**

**Features**

- Silicon NPN, To-72 packaged VHF/UHF Transistor
- 1.2 GHz Current-Gain Bandwidth Product @ 5mA IC
- Maximum Unilateral Gain – 12 dB (typ) @ 400 MHz



**DESCRIPTION:**

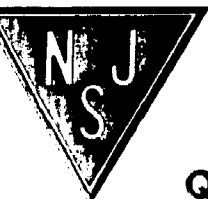
General Purpose small-signal, pre-driver, and driver, applications targeted for military and industrial equipment.

**ABSOLUTE MAXIMUM RATINGS** (T<sub>case</sub> = 25°C)

Symbol	Parameter	Value	Unit
V <sub>CEO</sub>	Collector-Emitter Voltage	10	Vdc
V <sub>CB0</sub>	Collector-Base Voltage	15	Vdc
V <sub>EB0</sub>	Emitter-Base Voltage	3.0	Vdc
I <sub>c</sub>	Collector Current	20	mA

**Thermal Data**

P <sub>D</sub>	Total Device Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C	200 1.14	mWatts mW/°C
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NJ Semi-Conductors reserves the right to change test conditions, parameters limits and package dimensions without notice information furnished by NJ Semi-Conductors is believed to be both accurate and reliable at the time of going to press. However NJ Semi-Conductors assumes no responsibility for any errors or omissions discovered in its use. NJ Semi-Conductors encourages customers to verify that datasheets are current before placing orders.

**Quality Semi-Conductors**

# ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

## STATIC

(off)

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
BVCEO	Collector-Emitter Breakdown Voltage (IC = 1.0 mA <sub>dc</sub> , IB = 0)	10	-	-	V <sub>dc</sub>
BVCBO	Collector-Base Breakdown Voltage (IC = 0.01 mA <sub>dc</sub> , IE = 0)	15	-	-	V <sub>dc</sub>
BVEBO	Emitter-Base Breakdown Voltage (IE = 0.01 mA <sub>dc</sub> , IC = 0)	3.0	-	-	V <sub>dc</sub>
ICBO	Collector Cutoff Current (VCE = 6.0 V <sub>dc</sub> , IE = 0 V <sub>dc</sub> )	-	1.0	10	nA

(on)

HFE	DC Current Gain (IC = 1.0 mA <sub>dc</sub> , VCE = 6.0 V <sub>dc</sub> )	25	-	300	-
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## DYNAMIC

Symbol	Test Conditions	Value			Unit
		Min.	Typ.	Max.	
f <sub>r</sub>	Current-Gain - Bandwidth Product (IC = 5.0 mA <sub>dc</sub> , VCE = 6 V <sub>dc</sub> , f = 100 MHz)	1200	-	2500	MHz
CCB	Output Capacitance (IC = 1.0 mA <sub>dc</sub> , VCE = 6 V <sub>dc</sub> , f = 450 MHz)	-	2.5	-	dB

## FUNCTIONAL

Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
G <sub>U max</sub>	Maximum Unilateral Gain (1)	IC = 1 mA <sub>dc</sub> , VCE = 6V <sub>dc</sub> , f = 400 MHz	-	12	-	dB
MAG	Maximum Available Gain	IC = 1 mA <sub>dc</sub> , VCE = 6V <sub>dc</sub> , f = 400 MHz	-	12.4	-	dB